



**DSS3540M** 

#### 40V PNP LOW V<sub>CE(sat)</sub> TRANSISTOR

#### **Features**

- $BV_{CEO} > -40V$
- I<sub>C</sub> = -500mA High Collector Current
- I<sub>CM</sub> = -1A Peak Pulse Current
- P<sub>D</sub> = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, V<sub>CE(sat)</sub>
- 0.60mm<sup>2</sup> Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DSS2540M
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

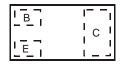


- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu @4 Solderable per MIL-STD-202, Method 208
- Weight: 0.0009 grams (Approximate)









**Bottom View** 

Device Symbol

Top View **Device Schematic** 

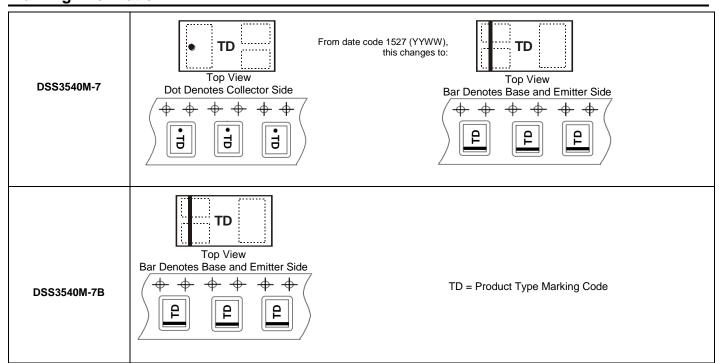
### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS3540M-7	TD	7	8	3,000
DSS3540M-7B	TD	7	8	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.</p>
  4. For packaging details, go to our website at http://www.diodes.com.

## Marking Information





# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current - Continuous	Ic	-500	mA
Peak Pulse Collector Current	I <sub>CM</sub>	-1	Α
Peak Base Current	I <sub>BM</sub>	-100	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	400		mW	
Power Dissipation	(Note 6)	- P <sub>D</sub>	1,000	THVV	
Thermal Resistance, Junction to Ambient	(Note 5)	310		°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	120	C/VV	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Rang	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 8)

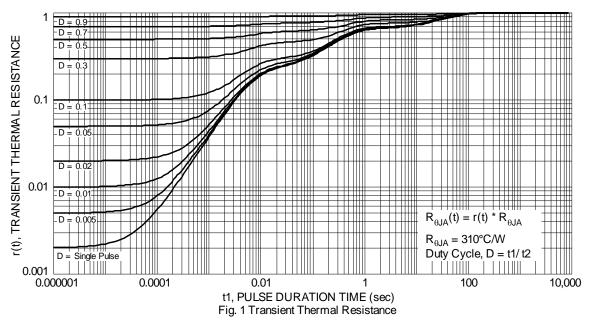
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	В

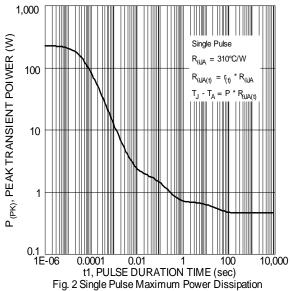
#### Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics**





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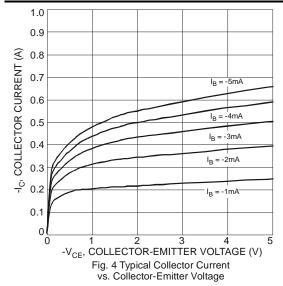
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

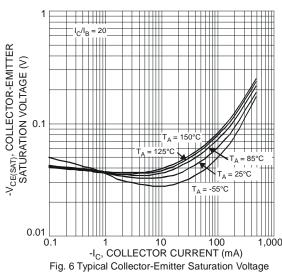
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40		_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-40	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_		V	$I_E = -100\mu A, I_C = 0$
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	-100 -50	nΑ μΑ	$V_{CB} = -30V, I_E = 0$ $V_{CB} = -30V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>		_	-100	nA	$V_{EB} = -5V, I_C = 0$
Collector-Emitter Cutoff Current			_	-100	nA	$V_{CE} = -30V, V_X = \pm 0.25V$
Collector-Emilier Cutoff Current	ICEX	_		-100	IIA	$V_{CE} = -30V, V_X = 3V$
Collector-Emitter Cutoff Current	I <sub>CES</sub>		_	-100	nA	V <sub>CE</sub> = -30V
ON CHARACTERISTICS (Note 9)						
DC Current Gain	hFE	200 150	_	_	_	$V_{CE} = -2V$ , $I_{C} = -10mA$ $V_{CE} = -2V$ , $I_{C} = -100mA$
	****	40	_	_		$V_{CE} = -2V, I_{C} = -500mA$
		_	_	-50		I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	_	-130	mV	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$
Collector-Emitter Saturation Voltage		_	_	-200		$I_C = -200 \text{mA}, I_B = -10 \text{mA}$
			_	-350		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Resistance	R <sub>CE(sat)</sub>		_	700	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	-1.2	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn On Voltage	V <sub>BE(on)</sub>	_	_	-1.1	V	$V_{CE} = -2V, I_{C} = -100mA$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>		_	10	pF	$V_{CB} = -10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	100	_	_	MHz	$V_{CE} = -5V$ , $I_{C} = -100$ mA, $f = 100$ MHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

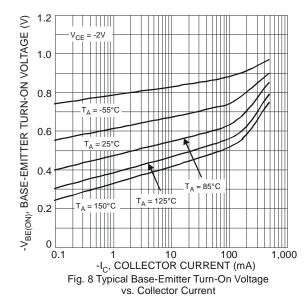


### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





vs. Collector Current



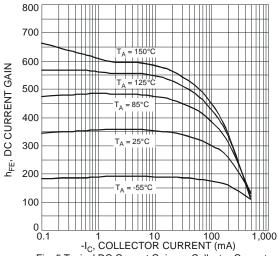


Fig. 5 Typical DC Current Gain vs. Collector Current

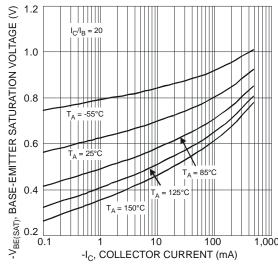


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

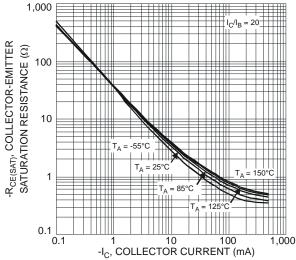
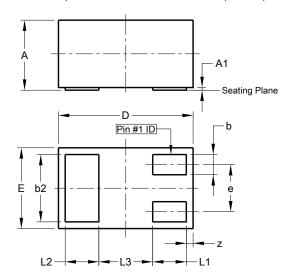


Fig. 9 Typical Collector-Emitter Saturation Resistance vs. Collector Current



# **Package Outline Dimensions**

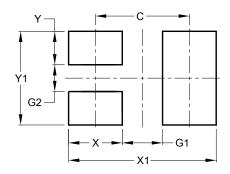
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
ם	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	-	-	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.70		
G1	0.30		
G2	0.20		
Х	0.40		
X1	1.10		
Υ	0.25		
Y1	0.70		



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